

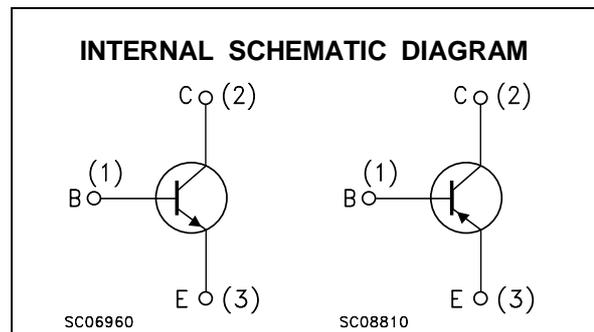
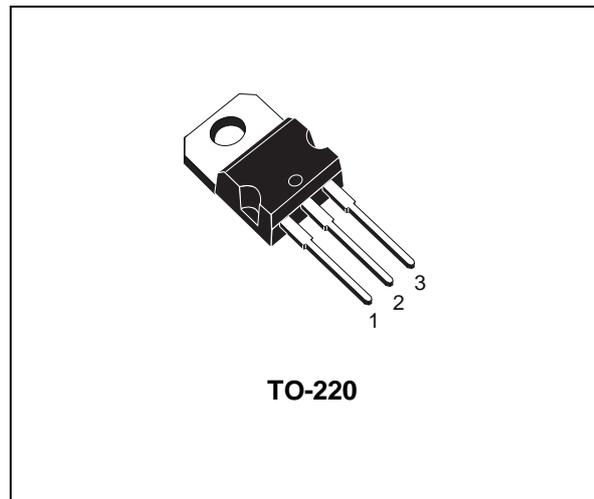
## COMPLEMENTARY SILICON POWER TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES

### DESCRIPTION

The BD909 and BD911 are silicon Epitaxial-Base NPN power transistors mounted in Jedec TO-220 plastic package. They are intended for use in power linear and switching applications.

The complementary PNP types are BD910 and BD912 respectively.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit	
		NPN	BD909		BD911
		PNP	BD910		BD912
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )		80	100	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )		80	100	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )		5		V
$I_E, I_C$	Collector Current		15		A
$I_B$	Base Current		5		A
$P_{tot}$	Total Dissipation at $T_c \leq 25^\circ\text{C}$		90		W
$T_{stg}$	Storage Temperature		-65 to 150		$^\circ\text{C}$
$T_j$	Max. Operating Junction Temperature		150		$^\circ\text{C}$

For PNP types voltage and current values are negative.

# BD909 / BD910 / BD911 / BD912

## THERMAL DATA

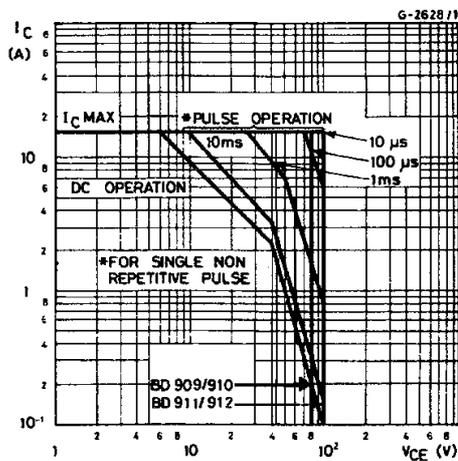
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1.4	°C/W
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## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CBO</sub>	Collector Cut-off Current (I <sub>E</sub> = 0)	for <b>BD909/910</b> V <sub>CB</sub> = 80 V for <b>BD911/912</b> V <sub>CB</sub> = 100 V T <sub>case</sub> = 150 °C for <b>BD909/910</b> V <sub>CB</sub> = 80 V for <b>BD911/912</b> V <sub>CB</sub> = 100 V			500 500 5 5	μA μA mA mA
I <sub>CEO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	for <b>BD909/910</b> V <sub>CE</sub> = 40 V for <b>BD911/912</b> V <sub>CE</sub> = 50 V			1 1	mA mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			1	mA
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 100 mA for <b>BD909/910</b> for <b>BD911/912</b>	80 100			V V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5 A I <sub>B</sub> = 0.5 A I <sub>C</sub> = 10 A I <sub>B</sub> = 2.5 A			1 3	V V
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 10 A I <sub>B</sub> = 2.5 A			2.5	V
V <sub>BE*</sub>	Base-Emitter Voltage	I <sub>C</sub> = 5 A V <sub>CE</sub> = 4 V			1.5	V
h <sub>FE*</sub>	DC Current Gain	I <sub>C</sub> = 0.5 A V <sub>CE</sub> = 4 V I <sub>C</sub> = 5 A V <sub>CE</sub> = 4 V I <sub>C</sub> = 10 A V <sub>CE</sub> = 4 V	40 15 5		250 150	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> = 0.5 A V <sub>CE</sub> = 4 V	3			MHz

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %  
For PNP types voltage and current values are negative.

## Safe Operating Area



## Derating Curves

